

**IN THE CLAIMS**

Please amend the claims as indicated below:

1-7. (Previously Withdrawn).

8. (Currently Amended) An on-chip signal transforming device, the device comprising:

a substrate substrate;

a first conductive layer above the substrate, wherein the first conductive layer has a first plurality of interleaved inductors, the first plurality of interleaved inductors formed completely within the first conductive layer; and

a second conductive layer above the substrate insulated from the first conductive layer, wherein the second conductive layer has at least one inductor, the at least one inductor formed completely within one or more layers other than the first conductive layer.

9. (Original) The device of claim 8, wherein the second conductive layer is below the first conductive layer.

10. (Currently Amended) The device of claim 8, wherein the at least one inductor is a second plurality of interleaved inductors.

11. (Original) The device of claim 8, wherein the at least one inductor is a spiral inductor.

12. (Currently Amended) The device of claim 8, further comprising:

a third conductive layer above the substrate insulated from the first and second conductive layers; and, wherein:

the at least one inductor is also partly formed in the third conductive layer, and the first conductive layer is in between the second conductive layer and the third conductive layer is above the first conductive layer.

13. (Currently Amended) An on-chip signal transforming device, the device comprising:  
a substrate substrate;  
a first conductive layer above the substrate, wherein the first conductive layer has a first plurality of interleaved inductors, the first plurality of interleaved inductors formed completely within the first conductive layer; and  
a second conductive layer above the substrate insulated from the first conductive layer, wherein the second conductive layer has a second plurality of interleaved inductors, the second plurality of interleaved inductors formed completely within the second conductive layer.

14. (Currently Amended) An on-chip signal transforming device, the device comprising:  
a substrate substrate;  
a first conductive layer above the substrate, wherein the first conductive layer has a first plurality of interleaved inductors, the first plurality of interleaved inductors formed completely within the first conductive layer; and  
a second conductive layer above the substrate, and below and insulated from the first conductive layer, wherein the second conductive layer has at least one inductor, the at least one inductor formed completely within one or more layers other than the first conductive layer;  
a third conductive layer in the insulator layer above the first conductive layer and insulated from the first and second conductive layers; and, wherein the at least one inductor is also partly formed in the third conductive layer and the first conductive layer is in between the second conductive layer and the third conductive layer.

15-18. (Previously Withdrawn).

19. (New) An on-chip signal transforming device, the device comprising:  
a substrate;  
a first conductive layer above the substrate, wherein the first conductive layer has a first spiral inductor and a second spiral inductor that are interleaved, the first spiral

inductor formed substantially within the first conductive layer and the second spiral inductor formed completely within the first conductive layer;  
a second conductive layer above the substrate insulated from the first conductive layer;  
and  
a conductive path from the first conductive layer to the second conductive layer and back to the first conductive layer to allow the first spiral inductor to cross over the second spiral inductor.

1.3

20. (New) The device according to claim 19, further comprising:  
a third conductive layer above the substrate and insulated from the first and second conductive layers, wherein the third conductive layer has a third spiral inductor that inductively couples to the first and second spiral inductors, the third spiral inductor formed completely within the third conductive layer.